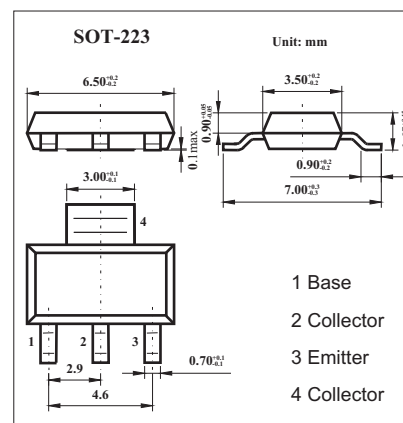


PNP General Purpose Transistor

PZTA56

■ Features

- Power dissipation: $P_c=1W$
- Collector current (DC): $I_c=500mA$
- Complementary NPN Type Available (PZTA06)



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0	V
Collector Current -Continuous	I_c	-500	mA
Collector Power Dissipation	P_D	1	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55 to 150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage	$V_{(BR)CBO}$	$I_c = -100 \mu A, I_E = 0$	-80			V
Collector-to-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c = -1 mA, I_B = 0$	-80			V
Emitter-to-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_c = 0$	-4.0			V
Collector cutoff current	I_{CBO}	$V_{CB} = -80 V, I_E = 0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{CE} = -4V, I_c = 0$			-100	nA
DC current gain	h_{FE}	$V_{CE} = -1.0V, I_c = -10mA$	100			
		$V_{CE} = -10V, I_c = -100mA$	100			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -100 mA, I_B = -10mA$			-0.25	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_c = -100 mA, V_{CE} = -1.0V$			-1.2	V
Transition frequency	f_T	$V_{CE} = -1.0V, I_c = -100mA, f = 100MHz$	50			MHz

■ Marking

Marking	A56
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